

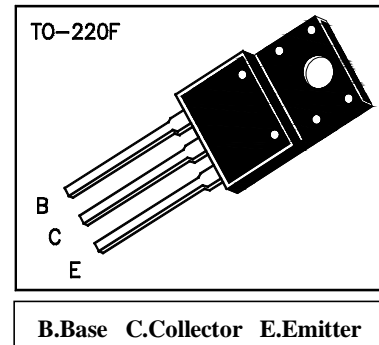
BU3150AF NPN Power Transistor

*Applications:

- ◆ Electrical Ballasts for fluorescent lighting
- ◆ Charger and Switch mode power supplies

*Features:

- ◆ High Current capacity
- ◆ High switching speed
- ◆ Wide safe operation area

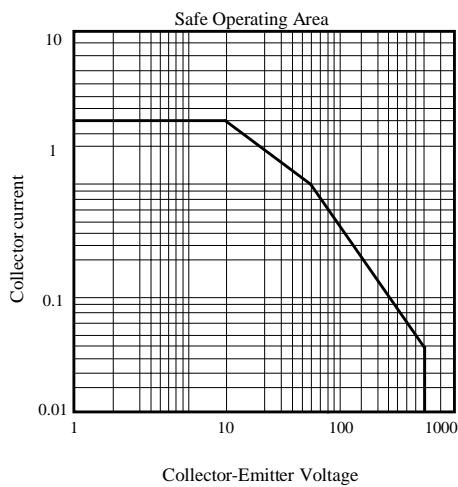
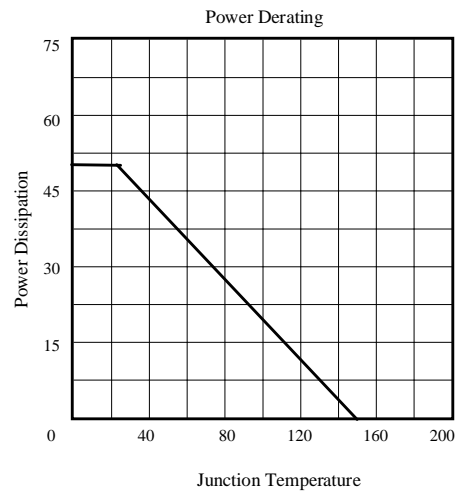
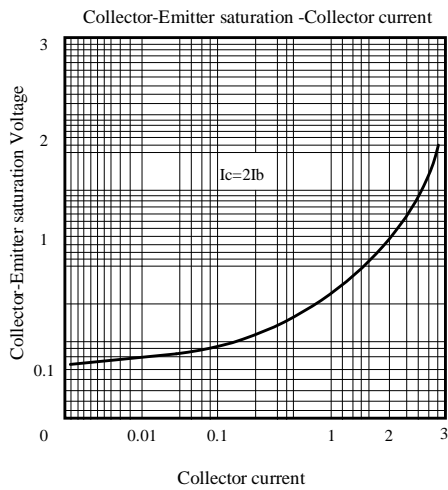
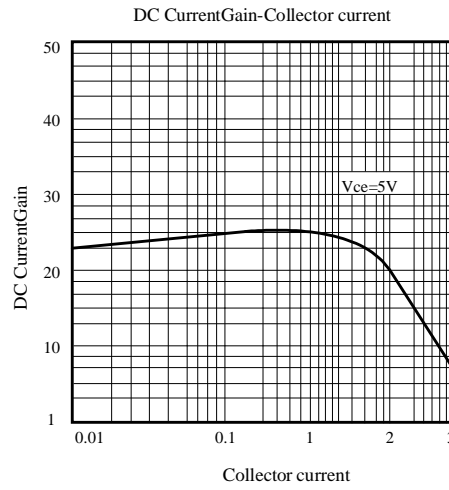
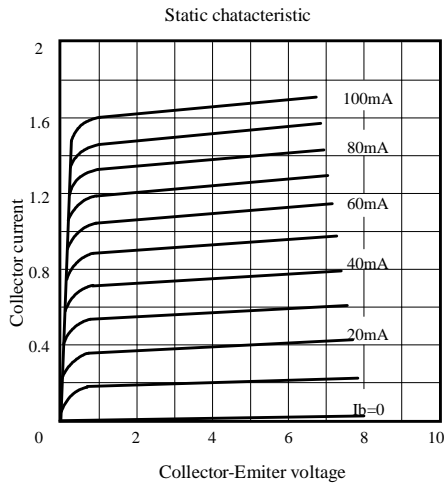
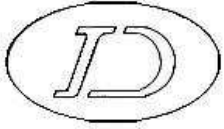


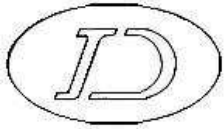
Absolute Maximum Ratings: (Tc=25°C unless specified)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	BV_{CEO}	≥ 800	V
Collector-Base Voltage	BV_{CBO}	≥ 1100	V
Emitter-Base Voltage	BV_{EBO}	≥ 9	V
Collector Current	I_{cm}	3	A
Total Power Dissipation	P_{cm}	50	W
Junction Temperature	T_{jm}	150	°C
Storage Temperature	T_{stg}	- 55 ~ 150	°C

Electronical Characteristic: (Tc=25°C unless specified)

Parameter	Symbol	Test conditions	Min.	Max.	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA; I_B=0$	800		V
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=1mA; I_E=0$	1100		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=1mA; I_C=0$	9		V
Collector-Emitter cut-off current	I_{CEO}	$V_{CE}=750V; I_B=0$		20	uA
Collector-Base cut-off current	I_{CBO}	$V_{CB}=1050V; I_E=0$		10	uA
Emitter-Base cut-off current	I_{EBO}	$V_{EB}=7V; I_C=0$		10	uA
DC Current Gain	H_{FE}	$V_{CE}=5V; I_C=0.2A$	15	35	
		$V_{CE}=5V; I_C=1mA$	8		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1A; I_B=0.5A$		0.6	V
Fall time	t_f	$I_C=1A; I_B=I_B=0.2A; V_{CE}=300V$		0.5	uS
Typical Frequency	f_T	$V_{CE}=10V; I_C=0.1A; f=1MHz$	4		MHz





Package Dimensions

TO-220F (Unit: mm, Tolerance ± 0.1 mm unless specified)

